



Advance Program Part II
LATE NEWS PAPERS

Wednesday, September 19

Oral Session

Room 201A Area 12

- 17:30 C-2-6L Magneto-transport properties of In_{0.56}Ga_{0.44}As gated-vertical quantum dot based on a metal-insulator-semiconductor structure
T. Kita^{1,2}, D. Chiba^{1,2}, Y. Ohno², H. Ohno^{1,2}, ¹ERATO-JST and ²Tohoku Univ. (Japan)
- 17:45 C-2-7L Electrical modulation of Curie temperature of (Ga,Mn)As channel in field-effect transistors: Mn composition dependence
Y. Nishitani¹, D. Chiba^{1,2}, F. Matsukura^{1,2} and H. Ohno^{1,2}, ¹Tohoku Univ. and ²ERATO-JST (Japan)

Room 304 Area 10

- 18:00 H-2-7L Experimental study of Ag/LiF/PFO interface for Top Emission PLEDs by synchrotron radiation photoemission spectroscopy
S. H. Chou¹, Y. H. Lu¹, C. W. Teng¹, K. C. Liu¹ and T. W. Pi², ¹Chang Gung Univ. and ²National Synchrotron Radiation Research Center (Taiwan)

Room 405 Area 9

- 17:30 I-2-5L Fabrication of Two-Layer stacked Poly-Si TFT CMOS Inverters Using Laser Crystallized channel with metal gate on Si Substrate
S. Y. Oh¹, C. G. Ahn¹, J. H. Yang¹, W. H. Lee², W. J. Cho² and M. G. Jang¹, ¹Electronics Telecommunications Research Inst. and ²Kwangwoon Univ. (Korea)

Thursday, September 20

Oral Session

Room 202B Area 8

- 10:15 F-3-6L New Finding of Pt Segregation at the NiSi/Si Interface by Atom Probe
H. Akutsu, H. Uchida, K. Nakamura, T. Iinuma and K. Suguro, *Toshiba Corp. (Japan)*

P-11, Area 11: Advanced Circuits and Systems

- P-11-12L pH Sensing Performance and Electrical Characterization on Hafnium Oxide Gate ISFETs with Single and Dual Stack Insulator by RF Sputtering
T. F. Lu, Y. C. Lin, C. M. Yang, C. S. Lai, D. G. Pijanowska and B. Jaroszewicz, *Chang Gung Univ. (Taiwan)*

P-12, Area 12: Spintronic Materials and Devices

- P-12-4L Perpendicularly Magnetized L1₀-FePt / MgO Epitaxially grown on GaAs for Electrical Spin Injection
M. Kohda^{1,2}, A. Ohtsu¹, T. Seki¹, A. Fujita¹, J. Nitta^{1,2} and K. Takanashi¹, ¹Tohoku Univ. and ²CREST-JST (Japan)

Friday, September 21

Oral Session

Room 102 Area 3

- 12:05 B-8-5L A Novel Embedded Extension SiGe (e²SiGe) Process for PFET Performance Enhancement for 45nm Technology and beyond
L. W. Teo¹, H. Utomo², S. S. Tan¹, S. Y. Ong¹, C. W. Lai¹, Z. Luo², S. D. Kim², R. Stierstorfer³, S. Mishra¹, H. Zhuang³, C. W. Yap¹, Y. Zhang², J. P. Han³, R. Lipton², J. Li², G. Chiulli², J. C. Kim⁴, B. F. Phoong¹, M. Eller³, X. Wu¹, Y. M. Lee¹, N. Rovedo², R. Wise², H. Shang², H. Ng² and J. Sudijono¹, ¹Chartered Semiconductor Manufacturing Ltd., ²IBM, ³Infineon Tech. and ⁴Samsung Electronics Co., Ltd. (USA)
- 12:20 B-8-6L Role of Source/Drain Electrodes in Ballistic Transport
K. Natori, *Univ. of Tsukuba (Japan)*

Room 202A Area 7

- 15:15 E-9-8L A Quantum Dot Swept Laser Source Based Upon a Multi Section Laser Device
B. J. Stevens, D. T. D. Childs, K. M. Groom and M. Hopkinson, R. A. Hogg, *Univ. of Sheffield (UK)*
- 15:45 E-9-10L Silicon Electro-Optic Modulator Fabricated on Silicon Substrate Utilizing the Three-Terminal Transistor Waveguide Structure
R. W. Chuang, Z. L. Liao, M. T. Hsu, J. C. Liao and C. C. Cheng, *National Cheng Kung Univ. (Taiwan)*

Room 202B Area 1

- 16:35 F-10-5L Defect Fermi level pinning models for HfO₂ : p-metal gates
J. Robertson, *Cambridge Univ. (UK)*

Room 202B Area 8

- 17:45 F-6-5L Oriented Growth of Location-Controlled Si Crystal Grains Using Ni Nano-Imprint and Excimer Laser Annealing
G. Nakagawa and T. Asano, *Kyushu Univ. (Japan)*

Poster Session (13:00-15:00, Multi-Purpose Hall)

P-1, Area 1: Advanced Gate Stack / Si Processing Science

- P-1-25L Oxygen-Vacancy-Induced Vt shift in La-containing Devices
B. J. O’Sullivan¹, R. Mitsuhashi², G. Pourtois¹, V. S. Chang³, C. Adelman¹, T. Schram¹, L. Å. Ragnarsson¹, N. Van der Heyden^{1,6}, H. J. Cho⁴, Y. Harada⁵, A. Veloso¹, R. O’Connor¹, L. Pantisano¹, H. Y. Yu¹, G. Groeseneken^{1,6}, P. Absil¹, S. Biesemans¹, A. Ikeda² and M. Niwa², ¹IMEC, ²Matsushita Ltd., ³TSMC, ⁴Samsung, ⁵Matsushita Electric Industrial Co., Ltd. and ⁶KU (Belgium)
- P-1-26L Physical Understanding of Determinant Factors for Φ_{eff} on La-based High-k
M. Suzuki, T. Shimizu and M. Koyama, *Toshiba Corp. (Japan)*
- P-1-27L In-situ Measurement of Temperature Variation in Si Wafer During Millisecond Rapid Thermal Annealing Induced by Thermal Plasma Jet Irradiation
H. Furukawa, S. Higashi, T. Okada, H. Kaku, H. Murakami and S. Miyazaki, *Hiroshima Univ. (Japan)*

P-3, Area 3: CMOS Devices/Device Physics

- P-3-27L A Comprehensive Study of Hot-Carrier Behaviors with Consideration of Non-Local, Series Resistance, Quantum, and Temperature Effects in Multi-Gate FinFETs
J. W. Han¹, D. Park² and Y. K. Choi¹, ¹KAIST and ²Samsung Electronics Co., Ltd. (Korea)
- P-3-28L Cross-Current SOI MOSFET Model and Important Aspects of CMOS Operations
Y. Azuma, Y. Yoshioka and Y. Omura, *Kansai Univ. (Japan)*
- P-3-29L A Comprehensive Modeling Study of Two-Dimensional Silicon Subbands Using a Full-Zone k.p Method
M. Szczap^{1,2}, N. Cavassilas², F. Michelini², F. Payet¹, F. Boeuf¹ and T. Skotnicki¹, ¹STMicroelectronics and ²L2MP (France)

P-4, Area 4: Advanced Memory Technology

- P-4-8L The impact of RTS on the Vt variation of 65nm MLC NOR flash memory
Y. Cai, W. H. Kwon, B. Y. Lee, J. I. Han, C. K. Park and S. Y. Heub, *Samsung Electronics Co., Ltd. (Korea)*

P-5, Area 5: Advanced Circuits and Systems

- P-5-12L Chip-to-Chip Power Delivery by Inductive Coupling with Ripple Canceling Scheme
Y. Yuxiang, Y. Yoshida, N. Yamagishi and T. Kuroda, *Keio Univ. (Japan)*

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Room 304 Area 9

- 14:45 H-9-6L OTFT-OLED Arrays using Screen Printing Process for Source and Drain Electrodes
G. S. Ryu, Y. B. Kim, H. J. Song and C. K. Song, *Dong-A Univ. (Korea)*

Room 405 Area 9

- 12:00 I-8-6L Photoresponse enhancement of metal-oxide-semiconductor near ultraviolet photodetector with multi-stack germanium quantum dots embedded in oxide
S. S. Tzeng and P. W. Li, *National Central Univ. (Taiwan)*
- 16:45 I-10-7L Nanoampere charge pumping by single-electron ratchet using Si nanowire MOSFETs
A. Fujiwara, K. Nishiguchi and Y. Ono, *NTT Corp. (Japan)*

Room 406 Area 13

- 16:30 J-10-6L Variation of Field Emission Property of Carbon Nanotube Field Emitters in Triode Structure Fabricated with Anodic Aluminum Oxide Templates
Y. Li, H. W. Cheng, C. C. Lin and F. M. Pan, *National Chiao Tung Univ. (Taiwan)*

UPDATED INFORMATION AND CORRECTION

Oral Session

Wednesday, September 19

Room 101 Area 1

- 14:00 A-1-1 (Invited)
Challenges for PMOS Metal Gate Electrodes and Solutions for Low Power Applications
J. K. Schaeffer, W. J. Taylor, S. B. Samavedam, D. C. Gilmer, D. H. Triyoso, R. I. Hegde, S. Kalpat, C. Capasso, M. Sadd, M. Stoker, A. Haggag, D. Roan and B. E. White Jr., *Freescale Semiconductor Inc. (USA)*

Room 201B Area 5

- 14:30 D-1-2 (Invited)
Characterization and Modeling of Layout Dependent Parametric Variability of Nanometer Devices
C. Guardiani, N. Dragone, M. Grottolo, E. Redaelli and S. Saxena, *PDF Solutions (Italy)*

Room 202B Area 8

- 14:00 F-1-1 (Invited)
InAs/In(Ga,Al)AsSb Quantum Dot Heterostructures for Photonic Devices
J. I. Chyi^{1,2}, P. C. Chiu¹, M. J. Shiau¹, T. P. Hsieh¹ and M. N. Chang³, ¹National Central Univ., ²Academia Sinica and ³National Nano Device Labs. (Taiwan)

- P-5-13L An Object Tracking Processor Core for Intelligent Surveillance System-on-Chip Applications
Y. K. Lai and Y. C. Chung, *National Chung Hsing Univ. (Taiwan)*

P-6, Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics

- P-6-11L Electroluminescence Characteristics of Yellow Luminescence-Like Defects in GaN HEMTs at Off-state Conditions
H. Chen, J. Lai, S. C. Kung, R. Penner and G. P. Li, *Univ. of California (USA)*

P-8, Area 8: Advanced Material Synthesis and Crystal Growth Technology

- P-8-19L Large Grain Poly-crystalline Si Films by Carbon Dioxide Laser Assisted SLG Method
H. Tsunazawa, Y. Taniguchi, S. Okazaki, M. Seki, Y. Otsuka, H. Takeuchi, M. Okamoto and J. Nakayama, *Sharp Corp. (Japan)*

P-9, Area 9: Structure, Conductance and Strength of Atomic-Sized Iridium Wires

- P-9-16L A Theoretical Study on Invisibility Devices based on Materials with Negative Refractive Index
T. Ochiai¹ and J. C. Nacher², ¹Toyama Prefectural Univ. and ²Future Univ. Hakodate (Japan)

P-10, Area 10: Organic Materials Science, Device Physics, and Applications

- P-10-11L Performance of organic thin film transistor using C₆₀/Au bilayer electrode
J. Park¹, S. Jung¹, H. J. Lee² and M. Yi¹, ¹Pusan National Univ. and ²SungKyunKwan Univ. (Korea)
- P-10-12L Reduction of Contact Resistance in Bottom Contact Pentacene-TFT by Employing Carrier Injection layer
D. Kumaki¹, T. Umeda² and S. Tokito^{1,2}, ¹Tokyo Tech. and ²NHK Sci. and Technical Research Labs. (Japan)
- P-10-13L Electroluminescent Characteristics of White OLED using (POB)₂Ir(pic)
D. E. Kim¹, B. S. Kim¹, B. J. Lee² and Y. S. Kwon¹, ¹Dong-A Univ. and ²Inje Univ. (Korea)
- P-10-14L Study of Single Strand DNA Hybridization Sensor on Gold Electrode of QCM by Electrochemical Determination
D. Y. Lee, C. Yang, W. S. Choi, S. H. Park and Y. S. Kwon, *Dong-A Univ. (Korea)*

Room 405 Area 9

- 16:15 I-2-1 (Invited)
Nanopatterned epitaxial graphene for nanoelectronics
C. Berger^{1,2}, X. Wu¹, X. Li¹, M. Sprinkle¹, Z. Song¹ and W. A. de Heer¹, ¹Georgia Inst. of Tech. and ²CNRS (USA)

Room 406 Area 4

- 16:15 J-2-1 (Invited)
S. M. Jung → J. H. Jeong

Thursday, September 20

Room 201A Area 12

- 17:00 C-6-1 (Invited)
The Magnetic Racetrack Memory: a novel spintronic device based on the current induced motion of domain walls
S. Parkin, *IBM (USA)*

Friday, September 21

Room 303 Area 6

- 9:00 G-7-1 (Invited)
Growth of InAs Channel HEMT Structure on Si substrate and It's Possible Application for Low Power Logic
E. Y. Chang¹, H. Yamaguchi^{2,3}, Y. C. Lin^{1,2}, M. Ueki⁴, Y. Hirayama^{2,3,5} and C. Y. Chang¹, ¹National Chiao Tung Univ., ²NTT Corp., ³Tohoku Univ., ⁴NTT Electronics Techno Corp. and ⁵SORST-JST (Taiwan)

Room 304 Area 10

- 9:00 H-7-1 (Invited)
Jet-printed Polymer Transistor Display Backplanes
R. A. Street, A. C. Arias and J. H. Daniel, *Palo Alto Research Center (USA)*

Oral Session → Poster Session

- I-2-5 → P-9-15
Structure, Conductance and Strength of Atomic-Sized Iridium Wires
T. Kizuka and M. Ryu, *Univ. of Tsukuba (Japan)*

Panelist addition

Rump Session B N. Koshida (Tokyo Univ. of Agri. & Tech.)

Session Chairs

- J-2 C. Hsu (eMemory Technology Inc.) → Y. Shimamoto (Hitachi, Ltd.)
E-3 R. Akimoto (AIST) → H. Kawashima (AIST)
J-3 C. Hsu (eMemory Technology Inc.) → Y. Yamauchi (Sharp Corp.)
E-7 R. Akimoto (AIST) → T. Hasama (AIST)
F-7 K. Kobayashi (Waseda Univ.) → M. Kobayashi (Waseda Univ.)

Session Time

Room 102	B-8	10:45 - 12:35	Room 304	H-2	16:15 - 18:15
Room 201A	C-2	16:15 - 18:00	Room 304	H-9	13:15 - 15:00
Room 202A	E-9	13:15 - 16:00	Room 405	I-8	10:45 - 12:15
Room 202B	F-3	9:00 - 10:30	Room 405	I-10	15:15 - 17:00
Room 202B	F-6	16:45 - 18:00	Room 406	J-10	15:15 - 16:45
Room 202B	F-10	15:15 - 16:50			

Affiliation

Steering Committee Vice - Chair
T. Mogami (NEC Corp.) → T. Mogami (Selete)

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SSDM 2007 Time Table

Wednesday, September 19											
Main Convention Hall											
10:00-12:30 PL: Opening Session/SSDM Award											
Room 101 (A)	Room 102 (B)	Room 201A (C)	Room 201B (D)	Room 202A (E)		Room 202B (F)	Room 303 (G)	Room 304 (H)	Room 405 (I)	Room 406 (J)	Multi-Purpose Hall (K)
14:00-15:50 Area 1: Advanced Gate Stack /Si Processing Science A-1: Metal Gate-I	14:00-16:00 Area 3: CMOS Devices/Device Physics B-1: Ge, SiGe Channel Transistor Technology	14:00-15:50 Area 2: Characterization and Materials Engineering for Interconnect Integration C-1: Novel Interconnects	14:00-15:50 Area 5: Advanced Circuits and Systems D-1: Scaling and Circuit Design Concern	14:00-16:00 Area 7: Photonic Devices and Device Physics E-1: Quantum-Dot Devices		14:00-16:00 Area 8: Advanced Material Synthesis and Crystal Growth Technology F-1: Compound Semiconductors	14:00-16:00 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics G-1: GaN FETs I	14:00-16:00 Area 10: Organic Materials Science, Device Physics, and Applications H-1: Organic Photo-Electronics	14:00-16:00 Area 9: Physics and Applications of Novel Functional Materials and Devices I-1: Novel Si Transistors	14:00-15:50 Area 4: Advanced Memory Technology J-1: DRAM I	
16:15-18:15 Area 1: Advanced Gate Stack /Si Processing Science A-2: Ge MIS	16:15-18:25 Area 3: CMOS Devices/Device Physics B-2: Transport in Nanoscale MOSFETs	16:15-18:00 Area 12: Spintronic Materials and Devices C-2: Spintronic Materials and Quantum Structures	16:15-18:15 Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices) D-2: MEMS Technology	16:15-18:15 Area 7: Photonic Devices and Device Physics E-2: Special Session: Photonic Crystals and Si Photonics I		16:15-17:30 Area 8: Advanced Material Synthesis and Crystal Growth Technology F-2: Oxides	16:15-18:00 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics G-2: GaN FETs II	16:15-18:15 Area 10: Organic Materials Science, Device Physics, and Applications H-2: Organic Light Emitting Devices	16:15-18:00 Area 9: Physics and Applications of Novel Functional Materials and Devices I-2: Transport Through Novel Materials and Structures	16:15-17:45 Area 4: Advanced Memory Technology J-2: Flash Memory I	
18:30-20:30 Banquet/Paper Award & Young Researcher Award (Multi-Purpose Hall 1F)											
Thursday, September 20											
Room 101 (A)	Room 102 (B)	Room 201A (C)	Room 201B (D)	Room 202A (E)		Room 202B (F)	Room 303 (G)	Room 304 (H)	Room 405 (I)	Room 406 (J)	Multi-Purpose Hall (K)
9:00-10:30 Area 1: Advanced Gate Stack /Si Processing Science A-3: Reliability-I	9:00-10:30 Area 3: CMOS Devices/Device Physics B-3: CMOS Integration	9:00-10:30 Area 2: Characterization and Materials Engineering for Interconnect Integration C-3: Plasma Induced Damage of Low-k Materials	9:00-10:30 Area 5: Advanced Circuits and Systems D-3: RF Components	9:00-10:30 Area 7: Photonic Devices and Device Physics E-3: Special Session: Photonic Crystals and Si Photonics II		9:00-10:30 Area 8: Advanced Material Synthesis and Crystal Growth Technology F-3: Group-IV Semiconductors I	9:00-10:15 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics G-3: High-Speed Devices and ICs I	9:00-10:30 Area 13: Applications of Nanotubes and Nanowires H-3: Nanowire & Nanotube Sensors		9:00-10:20 Area 4: Advanced Memory Technology J-3: Flash Memory II	(Poster setting)
10:45-12:15 Short Presentation Area 1	10:45-12:15 Short Presentation Area 3	10:45-12:15 Short Presentation Area 2 and Area 12	10:45-12:15 Short Presentation Area 5 and Area 11	10:45-12:15 Short Presentation Area 7		10:45-12:15 Short Presentation Area 8	10:45-12:15 Short Presentation Area 6	10:45-12:15 Short Presentation Area 10 and Area 13	10:45-12:15 Short Presentation Area 9	10:45-12:15 Short Presentation Area 4	
13:00-15:00 Poster Session (Multi-Purpose Hall 1F)											
15:15-16:25 Area 1: Advanced Gate Stack /Si Processing Science A-5: Junction	15:15-16:35 Area 3: CMOS Devices/Device Physics B-5: Mobility Characterization	15:15-16:45 Area 12: Spintronic Materials and Devices C-5: Symposium on Magnetic Tunnel Junctions and Beyond	15:15-16:15 Area 5: Advanced Circuits and Systems D-5: RF CMOS Circuits and Systems	15:15-16:30 Area 7: Photonic Devices and Device Physics E-5: Special Session: Photonic Crystals and Si Photonics III		15:15-16:30 Area 8: Advanced Material Synthesis and Crystal Growth Technology F-5: Group-IV Semiconductors II	15:15-16:15 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics G-5: High-Speed Devices and ICs II	15:15-16:30 Area 13: Applications of Nanotubes and Nanowires H-5: Nanowire Growth and Devices I		15:15-16:25 Area 4: Advanced Memory Technology J-5: PRAM	(Poster removed by 18:00)
16:45-18:05 Area 1: Advanced Gate Stack /Si Processing Science A-6: Reliability-II	16:45-18:05 Area 3: CMOS Devices/Device Physics B-6: Device Technology	17:00-18:00 Area 12: Spintronic Materials and Devices C-6: Symposium on Magnetic Tunnel Junctions and Beyond		16:45-18:00 Area 7: Photonic Devices and Device Physics E-6: Detectors and Sensors		16:45-18:00 Area 8: Advanced Material Synthesis and Crystal Growth Technology F-6: Group-IV Semiconductors III	16:45-18:00 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics G-6: Process and Characterization	16:45-17:45 Area 13: Applications of Nanotubes and Nanowires H-6: Nanowire Growth and Devices II		16:45-17:55 Area 4: Advanced Memory Technology J-6: ReRAM	
18:30-20:30 Rump Session		Room 101(A) “Oxide Electronics -Status and Outlook-” Room 102(B) “New Materials meet Advanced Silicon Technology”									
Friday, September 21											
Room 101 (A)	Room 102 (B)	Room 201A (C)	Room 201B (D)	Room 202A (E)		Room 202B (F)	Room 303 (G)	Room 304 (H)	Room 405 (I)	Room 406 (J)	Multi-Purpose Hall (K)
9:00-10:30 Area 1: Advanced Gate Stack /Si Processing Science A-7: Metal Gate-II	9:00-10:40 Area 3: CMOS Devices/Device Physics B-7: Stress Enhancement Technologies	9:00-10:30 Area 2: Characterization and Materials Engineering for Interconnect Integration C-7: Interconnects for RF and Mixed Signal Application	9:00-10:30 Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices) D-7: Nano-Bio Devices I	9:00-10:30 Area 7: Photonic Devices and Device Physics E-7: All-Optical Light Control		9:00-10:15 Area 8: Advanced Material Synthesis and Crystal Growth Technology F-7: Material Characterization	9:00-10:30 Area 6: Compound Semiconductor Circuits, Electron Devices and Device Physics G-7: Emerging Devices	9:00-10:30 Area 10: Organic Materials Science, Device Physics, and Applications H-7: Organic Transistor I		9:00-10:20 Area 4: Advanced Memory Technology J-7: DRAM II	
10:45-12:05 Area 1: Advanced Gate Stack /Si Processing Science A-8: High-k/Metal Gate Transistor	10:45-12:35 Area 3: CMOS Devices/Device Physics B-8: Modeling and Simulation	10:45-12:15 Area 2: Characterization and Materials Engineering for Interconnect Integration C-8: Interconnect Reliability	10:45-12:15 Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices) D-8: Nano-Bio Devices II	10:45-12:15 Area 7: Photonic Devices and Device Physics E-8: Lasers and LEDs				10:45-12:15 Area 10: Organic Materials Science, Device Physics, and Applications H-8: Organic Transistor II	10:45-12:15 Area 9: Physics and Applications of Novel Functional Materials and Devices I-8: Novel Nanostructure Devices	10:45-12:05 Area 4: Advanced Memory Technology J-8: FeRAM/MRAM	
13:15-14:55 Area 1: Advanced Gate Stack /Si Processing Science A-9: FUSI	13:15-14:55 Area 3: CMOS Devices/Device Physics B-9: Post Planar CMOS	13:15-15:05 Area 2: Characterization and Materials Engineering for Interconnect Integration C-9: Low-k and Airgap	13:15-14:45 Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices) D-9: Spectroscopy for Bio Sensing	13:15-16:00 Area 7: Photonic Devices and Device Physics E-9: LEDs		13:15-14:55 Area 1: Advanced Gate Stack/Si Processing Science F-9: Characterization	13:15-14:35 Area 5: Advanced Circuits and Systems G-9: Imaging Technology	13:15-15:00 Area 10: Organic Materials Science, Device Physics, and Applications H-9: Organic Transistor III	13:15-15:00 Area 9: Physics and Applications of Novel Functional Materials and Devices I-9: Quantum Dots and Qubits	13:15-15:00 Area 13: Applications of Nanotubes and Nanowires J-9: Carbon Nanotube Devices and Growth I	
	15:15-17:05 Area 3: CMOS Devices/Device Physics B-10: Noise and RF	15:25-16:25 Area 2: Characterization and Materials Engineering for Interconnect Integration C-10: Nanoscale Characterization	15:15-16:45 Area 11: Micro/Nano Electromechanical and Bio-Systems (Devices) D-10: μ -TAS and Medical Applications			15:15-16:50 Area 1: Advanced Gate Stack/Si Processing Science F-10: Advanced Process	15:15-16:35 Area 5: Advanced Circuits and Systems G-10: Connectivity		15:15-17:00 Area 9: Physics and Applications of Novel Functional Materials and Devices I-10: Novel Devices	15:15-16:45 Area 13: Applications of Nanotubes and Nanowires J-10: Carbon Nanotube Devices and Growth II	

SSDM 2007 Chairpersons List

Wednesday, September 19	Main Convention Hall		SSDM 2007 Chairpersons List							
	10:00-12:30 PL: Opening Session/SSDM Award									
	ROOM 101 (A)	ROOM 102 (B)	ROOM 201A (C)	ROOM 201B (D)	ROOM 202A (E)	ROOM 202B (F)	ROOM 303 (G)	ROOM 304 (H)	ROOM 405 (I)	ROOM 406 (J)
	A-1 (14:00-15:50) Y. Nara (Selete) Y. Yugami (Renesas Tech. Corp.)	B-1 (14:00-16:00) J. C. S. Woo (Univ. of California, Los Angeles) Y. Momiyama (Fujitsu Labs. Ltd.)	C-1 (14:00-15:50) T. Yoda (Toshiba Corp.) M. Nihei (Fujitsu Labs. Ltd.)	D-1 (14:00-15:50) H. Kobayashi (Gunma Univ.) T. Komuro (Agilent Technologies International Japan, Ltd.)	E-1 (14:00-16:00) M. Sugawara (Fujitsu Labs. Ltd.) M. Tokushima (NEC Corp.)	F-1 (14:00-16:00) M. Takahasi (JAEA) T. Fukui (Hokkaido Univ.)	G-1 (14:00-16:00) S. Tanaka (NEC Corp.) M. Kuzuhara (Univ. of Fukui)	H-1 (14:00-16:00) H. Usui (Tokyo Univ. of Agri. and Tech.) H. Kajii (Osaka Univ.)	I-1 (14:00-16:00) Y. Takahashi (Hokkaido Univ.) Y. Suda (Tokyo Univ. of Agri. and Tech.)	J-1 (14:00-15:50) I. Asano (Elpida Memory, Inc.) H. Jeong (Samsung Electronics Co., Ltd.)
Thursday, September 20	A-2 (16:15-18:15) S. Miyazaki (Hiroshima Univ.) H. Hwang (Gwangju Inst. of Sci. & Engineering)	B-2 (16:15-18:25) F. Boeuf (STMicroelectronics) Y. Kamakura (Osaka Univ.)	C-2 (16:15-18:00) Y. Ohno (Tohoku Univ.) S. Sugahara (Tokyo Tech.)	D-2 (16:15-18:15) M. Sasaki (Toyota Technological Inst.) O. Nakagawara (Murata Manufacturing Co., Ltd.)	E-2 (16:15-18:15) M. Sugawara (Fujitsu Labs. Ltd.) M. Tokushima (NEC Corp.)	F-2 (16:15-17:30) J. I. Chyi (National Central Univ.) H. Yamaguchi (NTT Basic Research Labs.)	G-2 (16:15-18:00) T. Tanaka (Matsushita Electric Industrial Co., Ltd.) Y. Ohno (Univ. of Tokushima)	H-2 (16:15-18:15) S. Tokito (NHK) M. Iwamoto (Tokyo Tech.)	I-2 (16:15-18:00) T. Fujisawa (NTT) K. Hirakawa (Univ. of Tokyo)	J-2 (16:15-17:45) Y. Yamauchi (Sharp Corp.) Y. Shimamoto (Hitachi, Ltd.)
	A-3 (9:00-10:30) J. Yugami (Renesas Tech. Corp.) Y. Tsunashima (Toshiba Corp.)	B-3 (9:00-10:30) K. Shibahara (Hiroshima Univ.) H. Wakabayashi (Sony Corp.)	C-3 (9:00-10:30) S. Ogawa (Selete) T. Tatsumi (Sony Corp.)	D-3 (9:00-10:30) R. Fujimoto (Toshiba Corp.) T. Hamasaki (Texas Instruments Japan Ltd.)	E-3 (9:00-10:30) M. Sugawara (Fujitsu Labs. Ltd.) H. Kawashima (AIST)	F-3 (9:00-10:30) K. Hiruma (Hokkaido Univ.) K. Nishi (NEC Corp.)	G-3 (9:00-10:15) S. Yamahata (NTT) Y. J. Chan (National Central Univ. Taiwan)	H-3 (9:00-10:30) K. Matsumoto (Osaka Univ.) Y. Cui (Stanford Univ.)		J-3 (9:00-10:20) Y. Shimamoto (Hitachi, Ltd.) Y. Yamauchi (Sharp Corp.)
	A-4 (10:45-12:15) H. Fukutome (Fujitsu Labs. Ltd.)	B-4 (10:45-12:15) S. Hayashi (Matsushita Electric Industrial Co., Ltd.)	C-4 (10:45-12:15) S. Ogawa (Selete)	D-4 (10:45-12:15) R. Fujimoto (Toshiba Corp.) H. Tabata (Univ. of Tokyo)	E-4 (10:45-12:15) M. Sugawara (Fujitsu Labs. Ltd.)	F-4 (10:45-12:15) H. Yamaguchi (NTT Corp.)	G-4 (10:45-12:15) M. Kuzuhara (Univ. of Fukui)	H-4 (10:45-12:15) T. Kamata (AIST) K. Matsumoto (Osaka Univ.)	I-4 (10:45-12:15) Y. Takahashi (Hokkaido Univ.)	J-4 (10:45-12:15) I. Asano (Elpida Memory, Inc.)
	A-5 (15:15-16:25) B. Mizuno (Ultimate Junction Technologies Inc.) H. Fukutome (Fujitsu Labs. Ltd.)	B-5 (15:15-16:35) Y. Kamakura (Osaka Univ.) K. Takeuchi (NEC Corp.)	C-5 (15:15-16:45) M. Tanaka (Univ. of Tokyo) K. Ando (AIST)	D-5 (15:15-16:15) K. Masu (Tokyo Tech.) T. Matsuoka (Osaka Univ.)	E-5 (15:15-16:30) M. Tokushima (NEC Corp.) M. Sugawara (Fujitsu Labs. Ltd.)	F-5 (15:15-16:30) K. Nishi (NEC Corp.) H. Yamaguchi (NTT Basic Research Labs.)	G-5 (15:15-16:15) S. Kuroda (Eudyna Devices Inc.) K. Maezawa (Univ. of Toyama)	H-5 (15:15-16:30) J. Motohisa (Hokkaido Univ.) T. Fukui (Hokkaido Univ.)		J-5 (15:15-16:25) M. Moniwa (Renesas Tech. Corp.) I. Asano (Elpida Memory, Inc.)
Friday, September 21	A-6 (16:45-18:05) K. Shiraishi (Univ. of Tsukuba) Y. Nara (Selete)	B-6 (16:45-18:05) K. Shibahara (Hiroshima Univ.) H. C. Lin (National Chiao Tung Univ.)	C-6 (17:00-18:00) K. Ando (AIST) M. Tanaka (Univ. of Tokyo)		E-6 (16:45-18:00) M. Gotoda (Mitsubishi Electric Corp.) M. Sugawara (Fujitsu Labs. Ltd.)	F-6 (16:45-18:00) R. Koch (Johannes Kepler Univ.) S. Shimomura (Ehime Univ.)	G-6 (16:45-18:00) A. Nakagawa (New Japan Radio Co., Ltd.) K. J. Chen (Hong Kong Univ. of Sci. and Tech.)	H-6 (16:45-17:45) K. Tateno (NTT) K. Ishibashi (RIKEN)		J-6 (16:45-17:55) K. Ito (NEC Corp.) Y. Shimamoto (Hitachi, Ltd.)
	A-7 (9:00-10:30) T. Nabatame (ASET) K. Shiraishi (Univ. of Tsukuba)	B-7 (9:00-10:40) F. Boeuf (STMicroelectronics) H. Wakabayashi (Sony Corp.)	C-7 (9:00-10:30) Y. Hayashi (NEC Corp.) M. Matsuura (Renesas Tech. Corp.)	D-7 (9:00-10:30) T. Nishimoto (Shimadzu Corp.) H. Tabata (Univ. of Tokyo)	E-7 (9:00-10:30) T. Hasama (AIST) Y. Lee (Hitachi, Ltd.)	F-7 (9:00-10:15) M. Kobayashi (Waseda Univ.) T. Iwai (Fujitsu Labs. Ltd.)	G-7 (9:00-10:30) T. Hashizume (Hokkaido Univ.) R. Hattori (Mitsubishi Electric Corp.)	H-7 (9:00-10:30) T. Minakata (Asahi-KASEI Corp.) K. Fujita (Kyushu Univ.)		J-7 (9:00-10:20) I. Asano (Elpida Memory, Inc.) M. Moniwa (Renesas Tech. Corp.)
	A-8 (10:45-12:05) H. Fukutome (Fujitsu Labs. Ltd.) Y. Tsunashima (Toshiba Corp.)	B-8 (10:45-12:35) A. Hokazono (Toshiba Corp.) Y. Momiyama (Fujitsu Labs. Ltd.)	C-8 (10:45-12:15) K. Ueno (Shibaura Inst. of Tech.) M. Kodera (Toshiba Corp.)	D-8 (10:45-12:15) I. Yamashita (Nara Inst. of Sci. and Tech.) S. Antoranz Contera (Univ. of Oxford)	E-8 (10:45-12:15) M. Ezaki (Toshiba Corp.) M. Gotoda (Mitsubishi Electric Corp.)			H-8 (10:45-12:15) K. Nomoto (Sony Corp.) K. Kudo (Chiba Univ.)	I-8 (10:45-12:15) M. Watanabe (Tokyo Tech.) H. Mizuta (Univ. of Southampton)	J-8 (10:45-12:05) T. Eshita (Fujitsu Ltd.) H. Jeong (Samsung Electronics Co., Ltd.)
	A-9 (13:15-14:55) T. Tatsumi (NEC Corp.) T. Nabatame (ASET)	B-9 (13:15-14:55) A. Hokazono (Toshiba Corp.) H. Sayama (Renesas Tech. Corp.)	C-9 (13:15-15:05) J. Koike (Tohoku Univ.) J. Gambino (IBM)	D-9 (13:15-14:45) K. Ajito (NTT) M. Niwano (Tohoku Univ.)	E-9 (13:15-16:00) Y. Lee (Hitachi Ltd.) M. Ezaki (Toshiba Corp.)	F-9 (13:15-14:55) S. Miyazaki (Hiroshima Univ.) H. Hwang (Gwangju Inst. of Sci. & Engineering)	G-9 (13:15-14:35) H. Yamauchi (Samsung Electronics Co., Ltd.) T. Matsuoka (Osaka Univ.)	H-9 (13:15-15:00) T. Kamata (AIST) T. Someya (Univ. of Tokyo)	I-9 (13:15-15:00) T. Usuki (Univ. of Tokyo) K. Ono (RIKEN)	J-9 (13:15-15:00) Y. Ochiai (JST) Y. Ohno (Nagoya Univ.)
		B-10 (15:15-17:05) D. Hisamoto (Hitachi Ltd.) K. Takeuchi (NEC Corp.)	C-10 (15:25-16:25) N. Hata (NEDO) S. Ogawa (Selete)	D-10 (15:15-16:45) K. Sawada (Toyohashi Univ. of Tech.) H. Tabata (Univ. of Tokyo)		F-10 (15:15-16:50) O. Faynot (CEA-LETI) T. Tatsumi (NEC Corp.)	G-10 (15:15-16:35) M. Horiguchi (Renesas Tech. Corp.) T. Komuro (Agilent Technologies International Japan, Ltd.)		I-10 (15:15-17:00) Y. Uraoka (Nara Inst. of Sci. and Tech.) B. G. Park (Seoul National Univ.)	J-10 (15:15-16:45) S. Akita (Osaka Prefecture Univ.) Y. Homma (Tokyo Univ. of Sci.)